CAS/STN FILE 'REGISTRY' ENTERED AT 14:22:10 ON 03 MAR 2005

L1	2	S	(METHYLSILANE/CN OR "METHYLSILANE (H3SIME)"/CN OR "METHYLSILANE ANION"/CN)
L2	1	S	"METHYLSILANE HOMOPOLYMER"/CN
L3	19	S	N.W/ELF OR N W/MF OR (COPPER OR ALUMINUM OR IRON OR BORON OR GALLIUM OR INDIUM OR TANTALUM OR MOLYBDENUM OR TUNGSTEN OR CHROMIUM OR VANADIUM OR NIOBIUM OR TITANIUM OR NICKEL OR IRIDIUM OR RHENIUM)/CN
L4	150	S	N.W/MF OR N W/ELF

FILE 'HCAPLUS' ENTERED AT 14:28:03 ON 03 MAR 2005

L6	88	S	(L1 OR L2) AND ((L3 OR L4) OR CONDUCTIVE(2A)(MATERIAL OR COMPOUND))
L7	4	S	(L1 OR L2)(L)EXPOS#######
L8	68	S	(L1 OR L2)(L)GAS
L9	79	S	(L1 OR L2)(L)VAPOR
L10	0	S	(L1 OR L2)(L)VAPOUR
L11	78	S	(L1 OR L2)(L)PLASMA
L12	27	S	(L1 OR L2)(L)COAT######
L13	135	S	(L1 OR L2)(L)DEPOSIT######
L14	4	S	(L1 OR L2)(L)PASSIVAT#####
L15	1	S	(L1 OR L2) AND NONOXIDI?
L16	1	S	(L1 OR L2) AND NON OXIDI?
L17	9	S	(L1 OR L2) AND PASSIVAT#####
L18	11	S	(L14 OR L15 OR L16 OR L17)
L19	44	S	L6 AND (L7 OR L8 OR L9 OR L10 OR L11 OR L12 OR L13)
L20	3	S	L18 AND L19
L21	0	S	L7 AND L19
L22	45	S	L6 AND (L7 OR L8 OR L9 OR L10 OR L11 OR L12 OR L13 OR L14 OR L15 OR L16 OR L17 OR L18 OR L19 OR L20 OR L21)
L23	42	S	L22 NOT L20
L24	32	S	L23 AND 1999-2005/PRY
L25	4	S	L23 AND 1992-1998/PRY
L26	5	S	L23 NOT P/DT
L27	4	S	L26 AND 1999-2005/PY
L28	1	S	L26 NOT L27
L29	38	S	L23 NOT L27
L30	6	S	L29 NOT L24
L31	8	S	L25 OR L28 OR L30
L32	20095	S	(METAL##### OR CONDUCT#####)(W)SUBSTRATE
L33	3	S	(L1 OR L2) AND L32
L34	0	S	L4 AND (L1 OR L2)

AB The metal, alloy, and/or ceramic powder layers on a compatible substrate are applied with the use of a preceramic polymer binder to obtain intermediate layers of a composite or cermet, with the polymer pyrolyzed in sintering to obtain a ceramic binder. The shrinkage of the composite or cermet interlayer with a functional gradient is controlled by adjusting the content of preceramic polymer binder. The **preceramic binder** is typically a poly (**methylsilane**), polycarbosilane, or a similar **polymer with Al, B, Ti, or Zr**. The process is suitable for applying Cu-SiC layer on Cu strip surface using the polycarbosilane precursor for Nicalon ceramic binder, and applying the 1st layer of Cu powder and then the 2nd layer of SiC powder with 10 mol% binder in each layer, followed by controlled firing under Ar atmospheric for bonding and sintering.

L133 ANSWER 13 OF 19 HCAPLUS **COPYRIGHT** ACS on STN
AN 1992:576384 HCAPLUS <DN 117:176384
ED Entered STN: 01 Nov 1992
TI **Deposition of tungsten films** from mixtures of tungsten hexafluoride, organohydrosilanes, and hydrogen
IN Roberts, David Allen; Garg, Diwakar; Lagendijk, Andre; Hochberg, Arthur Kenneth; Fine, Stephen Mark
PA Air Products and Chemicals, Inc., USA

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	EP 486927	A1	19920527	EP 1991-119282	19911112
	CA 2055422	AA	19920521	CA 1991-2055422	19911113
	JP 06256951	A2	19940913	JP 1991-331378	19911120
	US 5433975	A	19950718	US 1993-116178	19930902
PRAI	US 1990-616288	A	19901120		

OS MARPAT 117:176384
AB **W films** are chemical-vapor deposited on heated substrates by using H flow and simultaneously introducing a WF6-organohydroxysilane mixture The W films having a low elec. resistance and being essentially free of C, Si, and O are useful in the manufacture of integrated elec. circuits. Thus, **W was deposited on a Si wafer by reduction of WF6** at 230°. The flow rate of WF6, H2, diethylsilane, and Ar was 25, 300, 20, and 9000 cm3/min, resp. **After 15 min, the W film was 340 Å thick.** Under similar deposition conditions without the use of diethylsilane, the W film thickness was <150 Å.
IT Vapor deposition processes
(chemical, with tungsten, by reduction of tungsten hexafluoride by hydrogen and organohydroxysilanes)
IT **992-94-9, Methylsilane**
(**reduction** by hydrogen and, **of tungsten hexafluoride**, for chemical **vapor deposition of tungsten films**)

SEARCH HISTORY

FILE 'REGISTRY' ENTERED AT 13:27:31 ON 04 MAR 2005

L124	1	SEA ABB=ON	PLU=ON	METHYLSILANE/CN
L126	227	SEA ABB=ON	PLU=ON	TUNGSTEN/CN OR W/MF
L127	577	SEA ABB=ON	PLU=ON	N.W/MF OR N W/ELF OR TUNGSTEN NITRIDE
L128	51	SEA ABB=ON	PLU=ON	AL/MF OR ALUMINUM/CN

FILE 'HCAPLUS' ENTERED AT 13:30:53 ON 04 MAR 2005

L129	3361	SEA ABB=ON	PLU=ON	L124 OR METHYLSILANE OR METHYL SILANE OR SILYLMETHANE OR SILYL METHANE OR SILAETHANE OR MONOSILYLMETHANE
L130	63	SEA ABB=ON	PLU=ON	(L126 OR L127 OR L128) AND L129
L131	29920	SEA ABB=ON	PLU=ON	(L126 OR L127 OR L128)(L)(PLATE OR SLAB OR SUPPORT OR BASE OR SUBSTRATE OR SHEET OR WIRE OR WIRING)
L132	8	SEA ABB=ON	PLU=ON	L130 AND L131
L133	19	SEA ABB=ON	PLU=ON	METHYLSILANE(6A)(TUNGSTEN OR ALUMINUM OR AL OR WN OR (TUNGSTEN OR W)(W)NITRIDE OR (ELEMENTAL OR METAL####)(1A)W)

-----Original Message-----
From: Diaz, Jose